查询BQ4016供应商 捷多邦，专业PCB打样工厂，24小时加急出货

bq4016/bq4016Y

1024Kx8 Nonvolatile SRAM

Features

- Data retention in the absence of power
- Automatic write-protection during power-up/power-down cycles
- Conventional SRAM operation; unlimited write cycles
- 10-year minimum data retention in absence of power
- Battery internally isolated until power is applied

General Description

The CMOS bq4016 is a nonvolatile 8,388,608-bit static RAM organized as 1,048,576 words by 8 bits. The integral control circuitry and lithium energy source provide reliable nonvolatility coupled with the unlimited write cycles of standard SRAM.

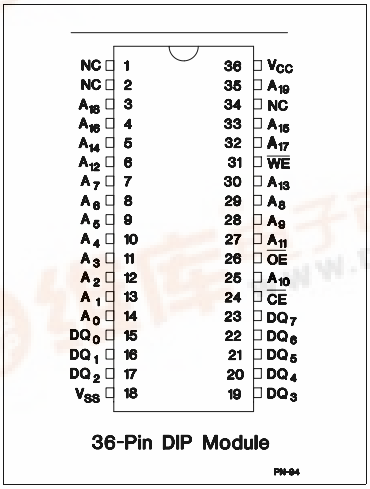
The control circuitry constantly monitors the single 5V supply for an out-of-tolerance condition. When V_{CC} falls out of tolerance, the SRAM is unconditionally write-protected to prevent an inadvertent write operation.

At this time the integral energy source is switched on to sustain the memory until after V_{CC} returns valid.

The bq4016 uses extremely low standby current CMOS SRAMs, coupled with a small lithium coin cell to provide nonvolatility without long write-cycle times and the write-cycle limitations associated with EEPROM.

The bq4016 has the same interface as industry-standard SRAMs and requires no external circuitry.

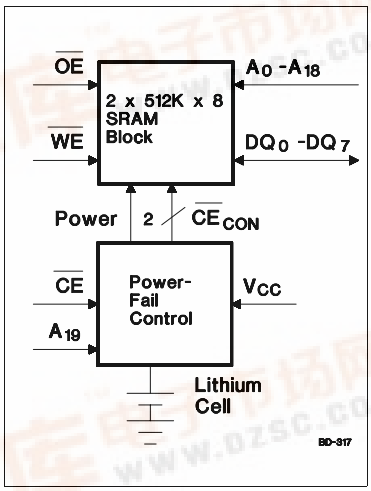
Pin Connections



Pin Names

A_0–A_{19}	Address inputs
DQ_0–DQ_7	Data input/output
$\overline{CE}$	Chip enable input
$\overline{OE}$	Output enable input
$\overline{WE}$	Write enable input
V_{CC}	+5 volt supply input
V_{SS}	Ground
NC	No connect

Block Diagram



Selection Guide

Part Number	Maximum Access Time (ns)	Negative Supply Tolerance	Part Number	Maximum Access Time (ns)	Negative Supply Tolerance
bq4016MC -70	70	-5%	bq4016YMC -70	70	-10%

Sept. 1996 B

找PDF 维库一下 pdf.dzsc.com

Functional Description

When power is valid, the bq4016 operates as a standard CMOS SRAM. During power-down and power-up cycles, the bq4016 acts as a nonvolatile memory, automatically protecting and preserving the memory contents.

Power-down/power-up control circuitry constantly monitors the V_{CC} supply for a power-fail-detect threshold V_{PFD}. The bq4016 monitors for V_{PFD} = 4.62V typical for use in systems with 5% supply tolerance. The bq4016Y monitors for V_{PFD} = 4.37V typical for use in systems with 10% supply tolerance.

When V_{CC} falls below the V_{PFD} threshold, the SRAM automatically write-protects the data. All outputs become high impedance, and all inputs are treated as "don't care." If a valid access is in process at the time of power-fail detection, the memory cycle continues to completion. If the memory cycle fails to terminate within time t_{WPT}, write-protection takes place.

As V_{CC} falls past V_{PFD} and approaches 3V, the control circuitry switches to the internal lithium backup supply, which provides data retention until valid V_{CC} is applied.

When V_{CC} returns to a level above the internal backup cell voltage, the supply is switched back to V_{CC}. After V_{CC} ramps above the V_{PFD} threshold, write-protection continues for a time t_{CER} (120ms maximum) to allow for processor stabilization. Normal memory operation may resume after this time.

The internal coin cells used by the bq4016 have an extremely long shelf life. The bq4016 provides data retention for more than 10 years in the absence of system power.

As shipped from Benchmarq, the integral lithium cells are electrically isolated from the memory. (Self-discharge in this condition is approximately 0.5% per year.) Following the first application of V_{CC}, this isolation is broken, and the lithium backup provides data retention on subsequent power-downs.

Truth Table

Mode	$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	I/O Operation	Power
Not selected	H	X	X	High Z	Standby
Output disable	L	H	H	High Z	Active
Read	L	H	L	D_{OUT}	Active
Write	L	L	X	D_{IN}	Active

Absolute Maximum Ratings

Symbol	Parameter	Value	Unit	Conditions
V_{CC}	DC voltage applied on V_{CC} relative to V_{SS}	-0.3 to 7.0	V	
V_T	DC voltage applied on any pin excluding V_{CC} relative to V_{SS}	-0.3 to 7.0	V	$V_T \le V_{CC} + 0.3$
T_{OPR}	Operating temperature	0 to +70	°C	
T_{STG}	Storage temperature	-40 to +70	°C	
T_{BIAS}	Temperature under bias	-10 to +70	°C	
T_{SOLDER}	Soldering temperature	+260	°C	For 10 seconds

Note: Permanent device damage may occur if **Absolute Maximum Ratings** are exceeded. Functional operation should be limited to the Recommended DC Operating Conditions detailed in this data sheet. Exposure to conditions beyond the operational limits for extended periods of time may affect device reliability.

Recommended DC Operating Conditions (TA = 0 to 70°C)

Symbol	Parameter	Minimum	Typical	Maximum	Unit	Notes
V_{CC}	Supply voltage	4.5	5.0	5.5	V	bq4016Y
		4.75	5.0	5.5	V	bq4016
V_{SS}	Supply voltage	0	0	0	V	
V_{IL}	Input low voltage	-0.3	-	0.8	V	
V_{IH}	Input high voltage	2.2	-	V_{CC} + 0.3	V	

Note: Typical values indicate operation at T_A = 25°C.

DC Electrical Characteristics (TA = 0 to 70°C, VCCmin ≤ VCC ≤ VCCmax)

Symbol	Parameter	Minimum	Typical	Maximum	Unit	Conditions/Notes
I_{LI}	Input leakage current	-	-	± 2	µA	$V_{IN} = V_{SS}$ to V_{CC}
I_{LO}	Output leakage current	-	-	± 2	µA	$\overline{CE} = V_{IH}$ or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$
V_{OH}	Output high voltage	2.4	-	-	V	I_{OH} = -1.0 mA
V_{OL}	Output low voltage	-	-	0.4	V	I_{OL} = 2.1 mA
I_{SB1}	Standby supply current	-	5	12	mA	$\overline{CE} = V_{IH}$
I_{SB2}	Standby supply current	-	2.5	5	mA	$0V \le V_{IN} \le 0.2V$, $\overline{CE} \ge V_{CC}$ - 0.2V, or $V_{IN} \ge V_{CC}$ - 0.2
I_{CC}	Operating supply current	-	75	115	mA	Min. cycle, duty = 100%, $\overline{CE} = V_{IL}$,$I_{I/O}$ = 0mA, A19 < V_{IL} or A19 > V_{IH},
V_{PFD}	Power-fail-detect voltage	4.55	4.62	4.75	V	bq4016
		4.30	4.37	4.50	V	bq4016Y
V_{SO}	Supply switch-over voltage	-	3	-	V	

Note: Typical values indicate operation at T_A = 25°C, V_{CC} = 5V.

Capacitance (T_A = 25°C, F = 1MHz, V_{CC} = 5.0V)

Symbol	Parameter	Minimum	Typical	Maximum	Unit	Conditions
$C_{I/O}$	Input/output capacitance	-	-	20	pF	Output voltage = 0V
C_{IN}	Input capacitance	-	-	20	pF	Input voltage = 0V

Note: These parameters are sampled and not 100% tested.

AC Test Conditions

Parameter	Test Conditions
Input pulse levels	0V to 3.0V
Input rise and fall times	5 ns
Input and output timing reference levels	1.5 V (unless otherwise specified)

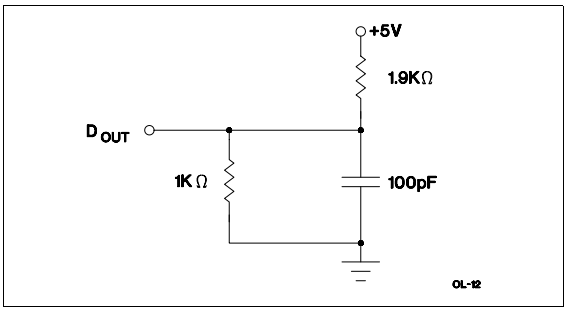


Figure 1. Output Load A

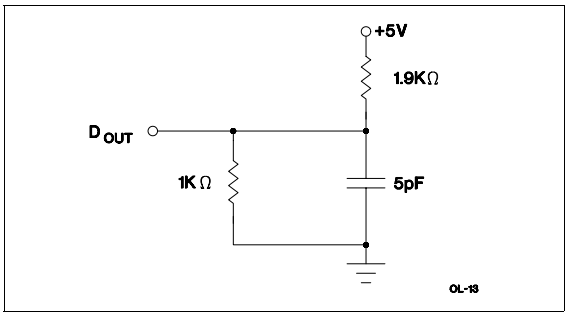
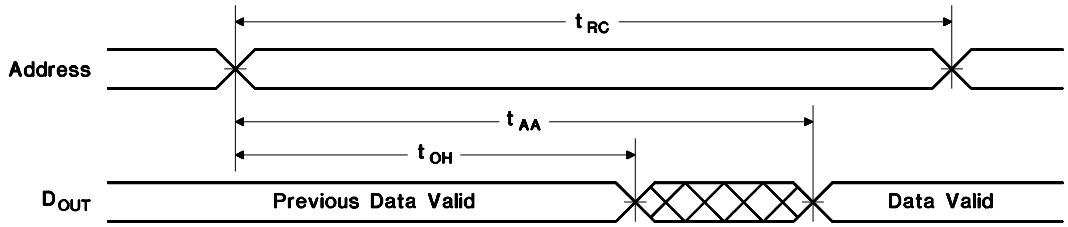


Figure 2. Output Load B

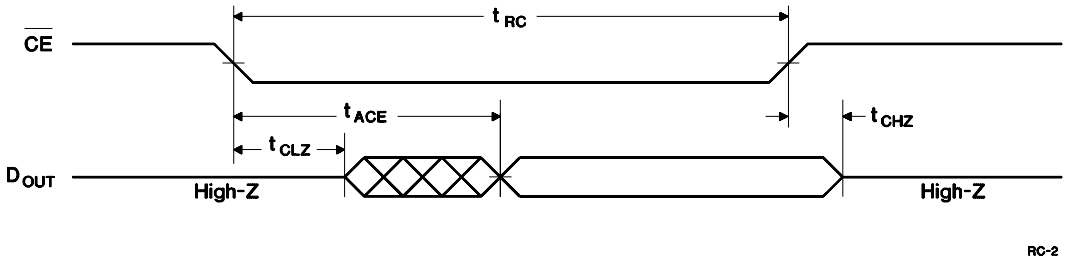
Read Cycle (T_A = 0 to 70°C, $V_{CCmin} \leq V_{CC} \leq V_{CCmax}$)

Symbol	Parameter	-70		Unit	Conditions
		Min.	Max.		
t_{RC}	Read cycle time	70	-	ns	
t_{AA}	Address access time	-	70	ns	Output load A
t_{ACE}	Chip enable access time	-	70	ns	Output load A
t_{OE}	Output enable to output valid	-	35	ns	Output load A
t_{CLZ}	Chip enable to output in low Z	5	-	ns	Output load B
t_{OLZ}	Output enable to output in low Z	5	-	ns	Output load B
t_{CHZ}	Chip disable to output in high Z	0	25	ns	Output load B
t_{OHZ}	Output disable to output in high Z	0	25	ns	Output load B
t_{OH}	Output hold from address change	10	-	ns	Output load A

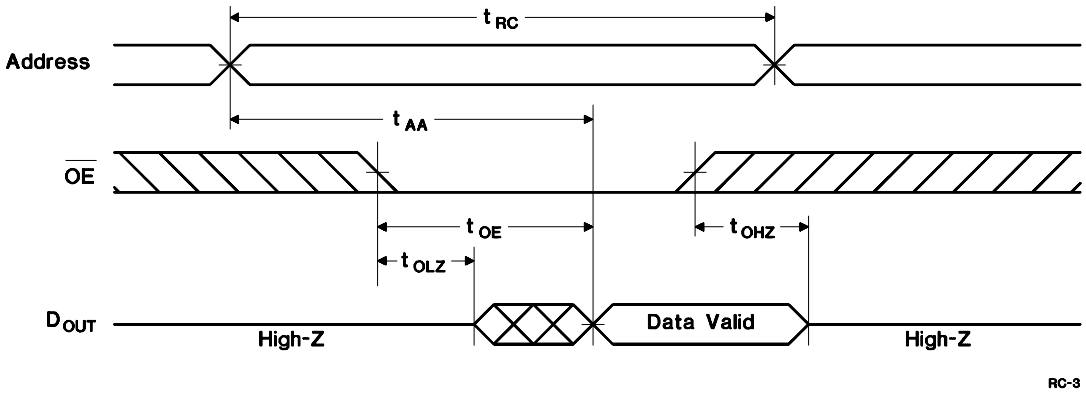
Read Cycle No. 1 (Address Access) [1,2]



Read Cycle No. 2 ($\overline{CE}$ Access) [1,3,4]



Read Cycle No. 3 ($\overline{OE}$ Access) [1,5]



Notes:
1. $\overline{WE}$ is held high for a read cycle.
2. Device is continuously selected: $\overline{CE}$ = $\overline{OE}$ = V_{IL}.
3. Address is valid prior to or coincident with $\overline{CE}$ transition low.
4. $\overline{OE}$ = V_{IL}.
5. Device is continuously selected: $\overline{CE}$ = V_{IL}.

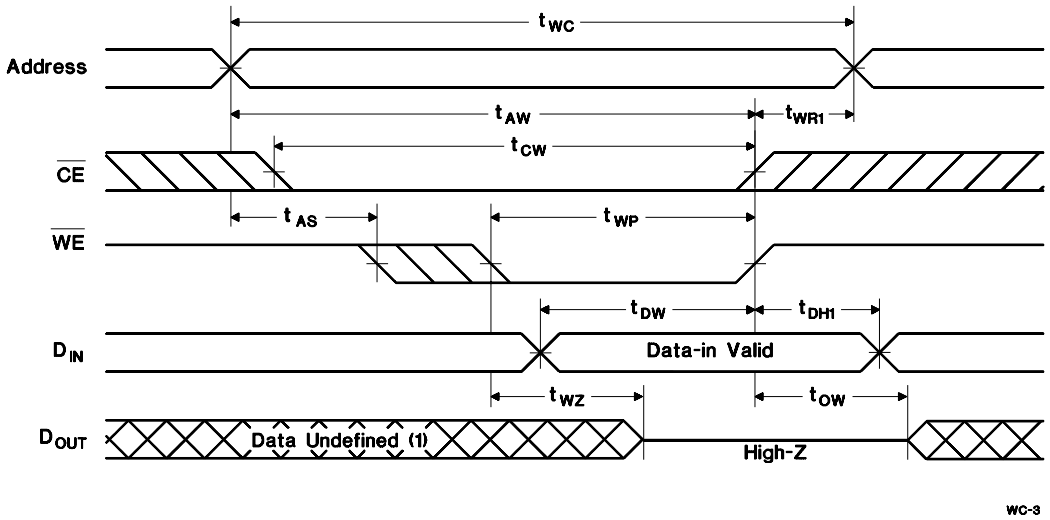
Write Cycle (T_A = 0 to 70°C, $V_{CCmin} \leq V_{CC} \leq V_{CCmax}$)

Symbol	Parameter	-70		Units	Conditions/Notes
		Min.	Max.		
t_{WC}	Write cycle time	70	-	ns	
t_{CW}	Chip enable to end of write	65	-	ns	(1)
t_{AW}	Address valid to end of write	65	-	ns	(1)
t_{AS}	Address setup time	0	-	ns	Measured from address valid to beginning of write. (2)
t_{WP}	Write pulse width	55	-	ns	Measured from beginning of write to end of write. (1)
t_{WR1}	Write recovery time (write cycle 1)	5	-	ns	Measured from $\overline{WE}$ going high to end of write cycle. (3)
t_{WR2}	Write recovery time (write cycle 2)	15	-	ns	Measured from $\overline{CE}$ going high to end of write cycle. (3)
t_{DW}	Data valid to end of write	30	-	ns	Measured to first low-to-high transition of either $\overline{CE}$ or $\overline{WE}$.
t_{DH1}	Data hold time (write cycle 1)	0	-	ns	Measured from $\overline{WE}$ going high to end of write cycle. (4)
t_{DH2}	Data hold time (write cycle 2)	10	-	ns	Measured from $\overline{CE}$ going high to end of write cycle. (4)
t_{WZ}	Write enabled to output in high Z	0	25	ns	I/O pins are in output state. (5)
t_{OW}	Output active from end of write	5	-	ns	I/O pins are in output state. (5)

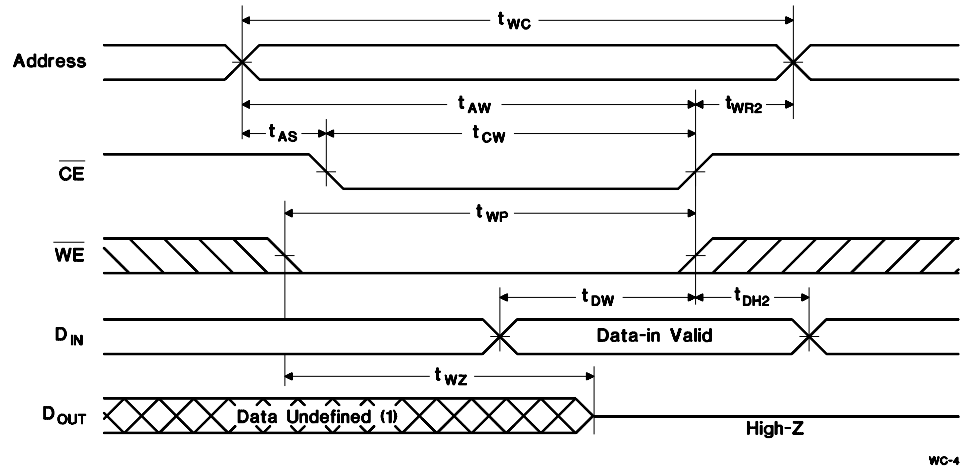
Notes:

1. A write ends at the earlier transition of $\overline{CE}$ going high and $\overline{WE}$ going high.
2. A write occurs during the overlap of a low $\overline{CE}$ and a low $\overline{WE}$. A write begins at the later transition of $\overline{CE}$ going low and $\overline{WE}$ going low.
3. Either t_{WR1} or t_{WR2} must be met.
4. Either t_{DH1} or t_{DH2} must be met.
5. If $\overline{CE}$ goes low simultaneously with $\overline{WE}$ going low or after $\overline{WE}$ going low, the outputs remain in high-impedance state.

Write Cycle No. 1 ($\overline{WE}$-Controlled) [1,2,3]



Write Cycle No. 2 ($\overline{CE}$-Controlled) [1,2,3,4,5]



Notes:

1. $\overline{CE}$ or $\overline{WE}$ must be high during address transition.
2. Because I/O may be active ($\overline{OE}$ low) during this period, data input signals of opposite polarity to the outputs must not be applied.
3. If $\overline{OE}$ is high, the I/O pins remain in a state of high impedance.
4. Either t_{WR1} or t_{WR2} must be met.
5. Either t_{DH1} or t_{DH2} must be met.

Power-Down/Power-Up Cycle (T_A = 0 to 70°C)

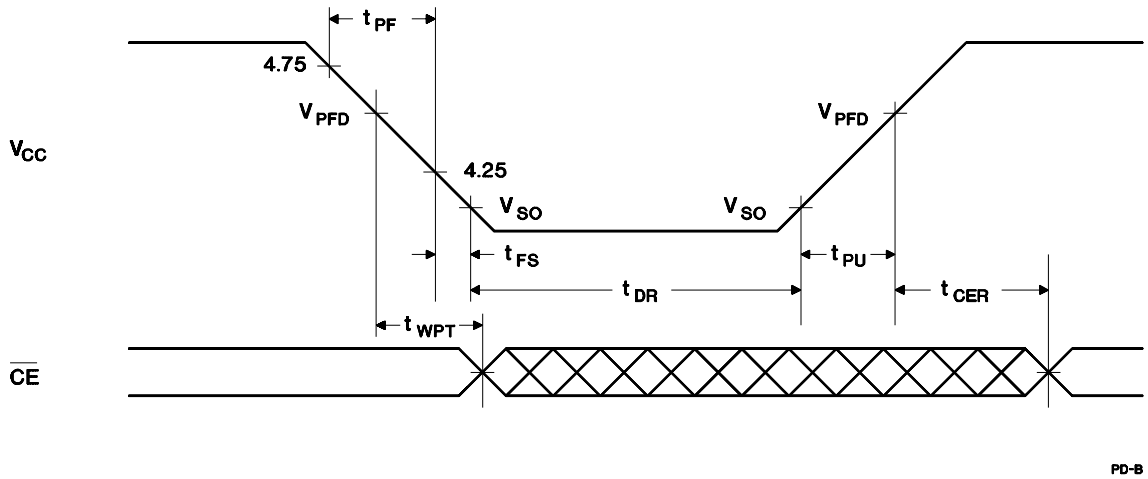
Symbol	Parameter	Minimum	Typical	Maximum	Unit	Conditions
t_{PF}	V_{CC} slew, 4.75 to 4.25 V	300	-	-	µs	
t_{FS}	V_{CC} slew, 4.25 to V_{SO}	10	-	-	µs	
t_{PU}	V_{CC} slew, V_{SO} to V_{PFD} (max.)	0	-	-	µs	
t_{CER}	Chip enable recovery time	40	80	120	ms	Time during which SRAM is write-protected after V_{CC} passes V_{FPD} on power-up.
t_{DR}	Data-retention time in absence of V_{CC}	10	-	-	years	T_A = 25°C. (2)
t_{WPT}	Write-protect time	40	100	150	µs	Delay after V_{CC} slews down past V_{PFD} before SRAM is write-protected.

Notes: 1. Typical values indicate operation at T_A = 25°C, V_{CC} = 5V.

2. Batteries are disconnected from circuit until after V_{CC} is applied for the first time. t_{DR} is the accumulated time in absence of power beginning when power is first applied to the device.

Caution: Negative undershoots below the absolute maximum rating of -0.3V in battery-backup mode may affect data integrity.

Power-Down/Power-Up Timing



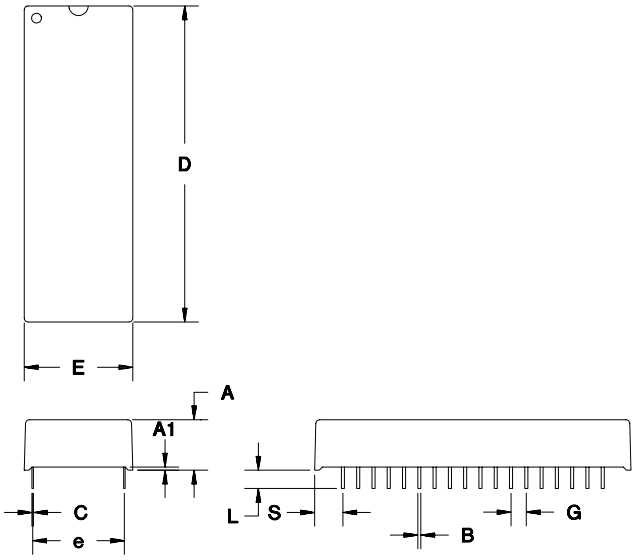
PD-B

Data Sheet Revision History

Change No.	Page No.	Description
1	All	Changed from “Preliminary” to “Final” data sheet

Notes: Change 1 = Sept 1996 B changes from June 1995.
.

MC: 36-Pin C-Type Module

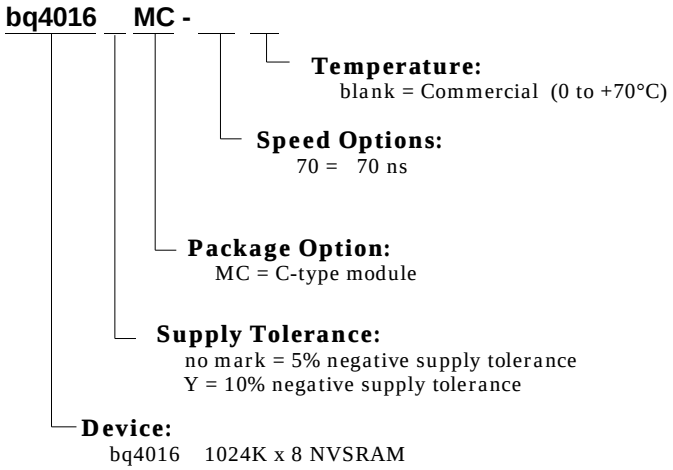


36-Pin MC (C-Type Module)

Dimension	Minimum	Maximum
A	0.365	0.375
A1	0.015	-
B	0.017	0.023
C	0.008	0.013
D	2.070	2.100
E	0.710	0.740
e	0.590	0.630
G	0.090	0.110
L	0.120	0.150
S	0.175	0.210

All dimensions are in inches.

Ordering Information



IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 1999, Texas Instruments Incorporated